

Patent  
10/010,484

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hshieh et al.  
Serial No.: 10/010,484  
Filed: November 20, 2001  
Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure  
Art Unit: 2826  
Examiner: Tan N. Tran  
Docket No.: GS 150  
Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

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**PETITION UNDER 37 CFR 1.136(a) and**  
**SECOND RESPONSE AFTER FINAL REJECTION**

Sir:

Applicants hereby petition the Assistant Commissioner to grant a three (3) month extension of time, up to and including January 23, 2004, in which to respond to the Office Action dated July 23, 2003 (Paper No. 12) in the above-identified application. The extension fee in the amount of \$950.00 may be charged to deposit account No. 50-1047. In addition, any deficiencies may be charged to deposit account No. 50-1047. In further response to the second final Office Action dated July 23, 2003 (Paper No. 12), a previous response having been filed on October 23, 2003, kindly amend the application and consider the following remarks.

**Certificate of Facsimile Transmission**

I hereby certify that this document and any document referenced herein has been transmitted via facsimile to the US Patent and Trademark Office at (703) 872-9319 on 1/23/04.

Marjorie I. Scariati  
(Printed Name of Person Mailing Correspondence)

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(Signature)